

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	30mΩ@10V	20A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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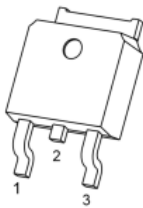
Feature

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

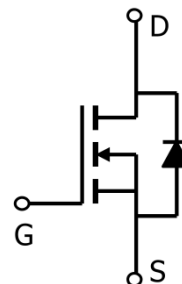
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Package

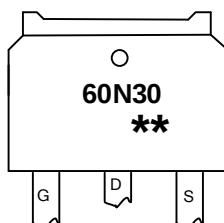


TO-252(G:1 D:2 S:3)

Circuit diagram



Marking



60N30 : Product code
** : Week code.

Order Information

Device	Package	Unite/Tape
SP60N30TH	TO-252	2500

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	20	A
Drain Current-Continuous($T_C=100^\circ\text{C}$)	I_D	14	A
Pulsed Drain Current	I_{DM}	56	A
Maximum Power Dissipation	P_D	40	W
Derating factor		0.27	W/°C
Single pulse avalanche energy ⁽¹⁾	E_{AS}	72	mJ
Thermal Resistance,Junction-to-Case ⁽²⁾	$R_{\theta JC}$	3.7	°C/W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

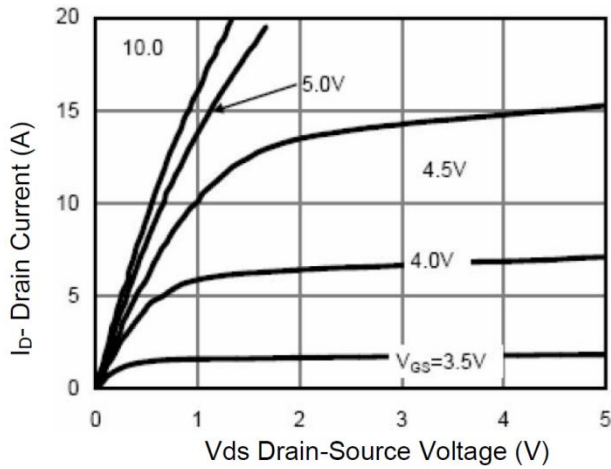
Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ⁽³⁾						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	30	43	mΩ
Dynamic Characteristics ⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	590	-	PF
Output Capacitance	C _{oss}		-	60	-	PF
Reverse Transfer Capacitance	C _{rss}		-	25	-	PF
Switching Characteristics ⁽⁴⁾						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =2A, V _{GS} =10V, R _G =3Ω, R _L =6.7Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	2.6	-	nS
Turn-Off Delay Time	t _{d(off)}		-	16.1	-	nS
Turn-Off Fall Time	t _f		-	2.3	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =4.5A, V _{GS} =10V	-	14	-	nC
Gate-Source Charge	Q _{gs}		-	2.9	-	nC
Gate-Drain Charge	Q _{gd}		-	5.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V _{SD}	V _{GS} =0V, I _S =1A	-	-	1.2	V
Diode Forward Current ⁽²⁾	I _S		-	-	20	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =20A di/dt = 100A/μs ⁽³⁾	-	35	-	nS
Reverse Recovery Charge	Q _{rr}		-	53	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

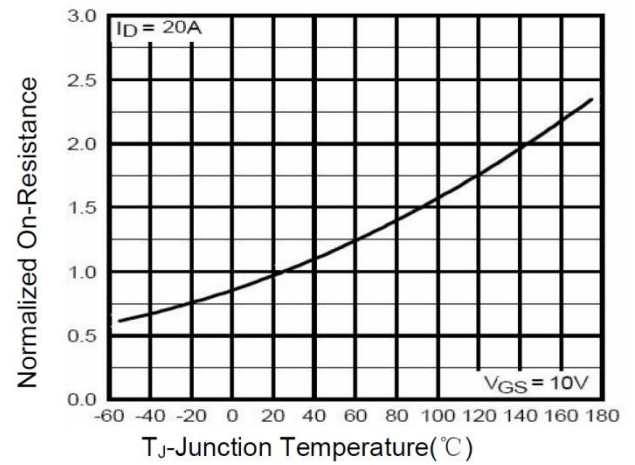
Notes:

1. E_{AS} condition: $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

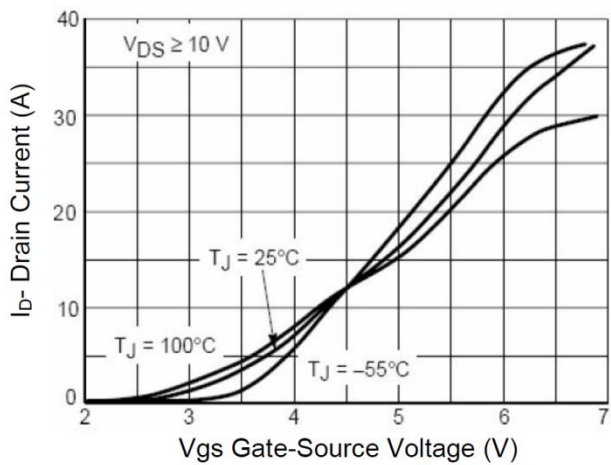
Typical Characteristics



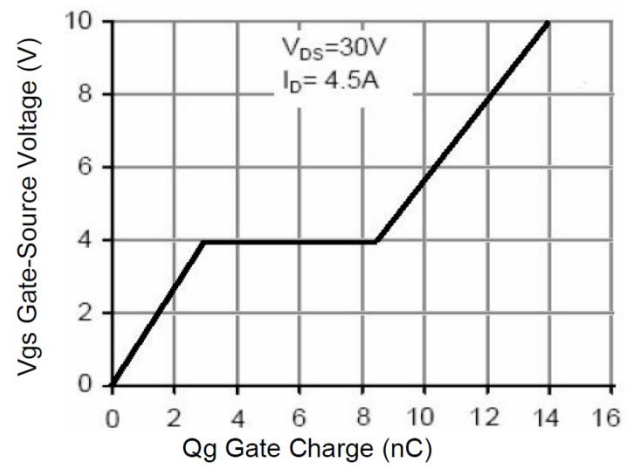
Output Characteristics



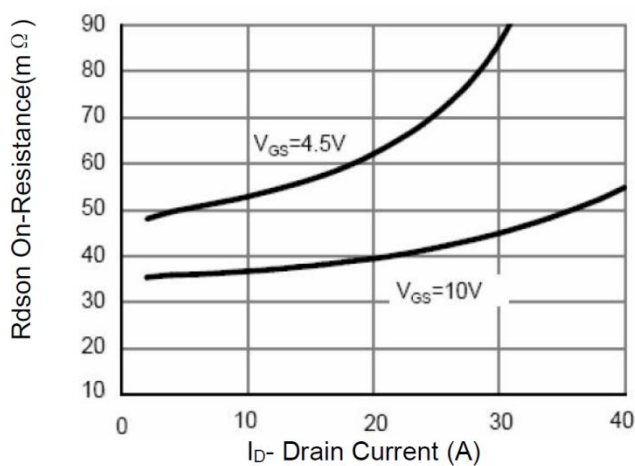
Rdson-Junction Temperature



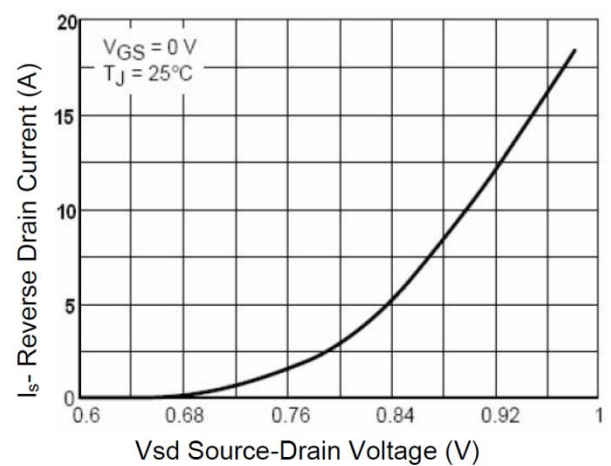
Transfer Characteristics



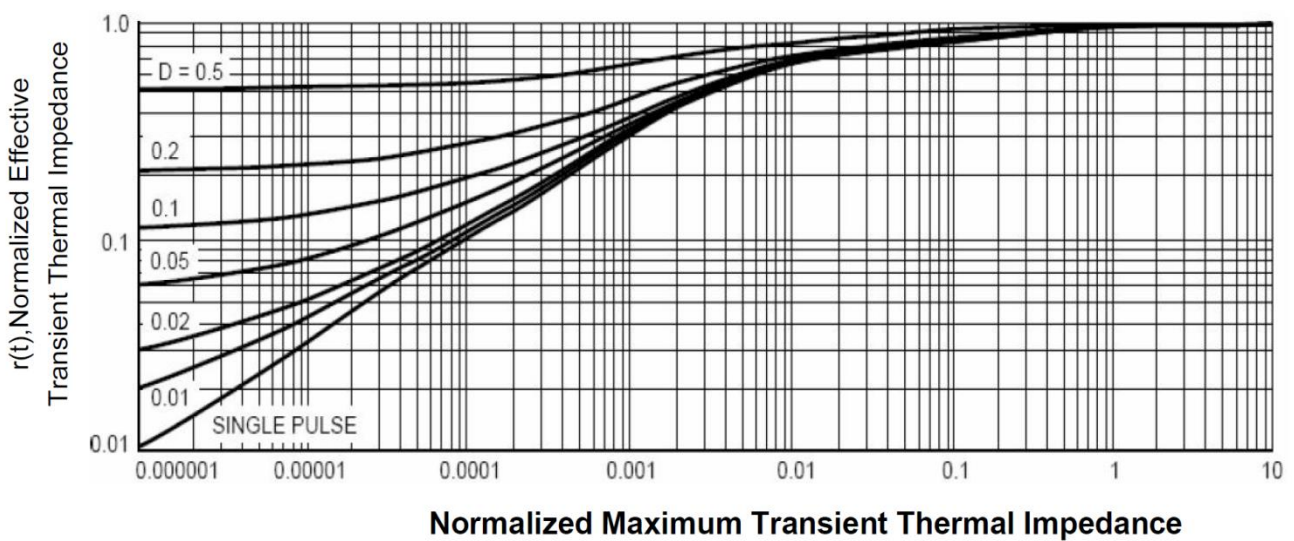
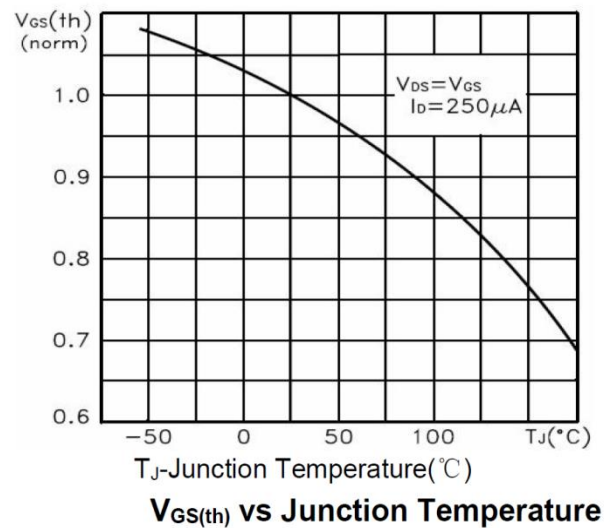
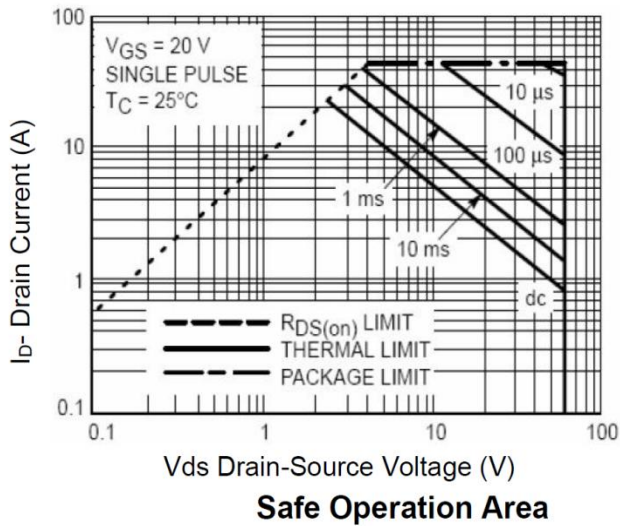
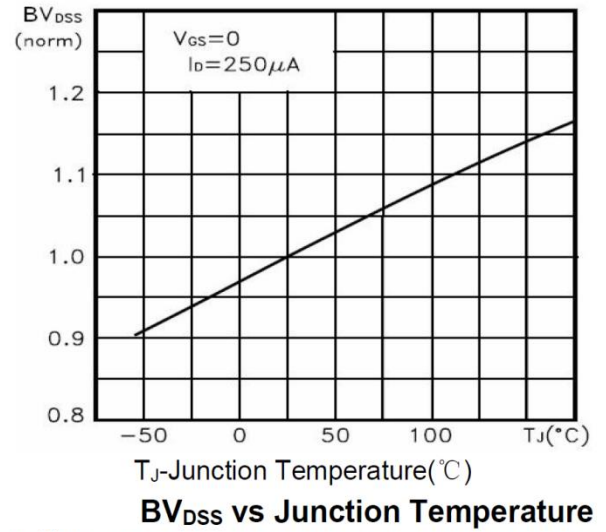
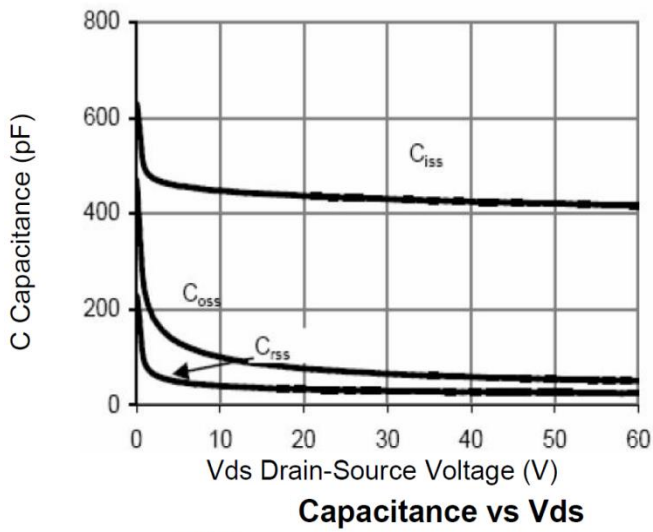
Gate Charge



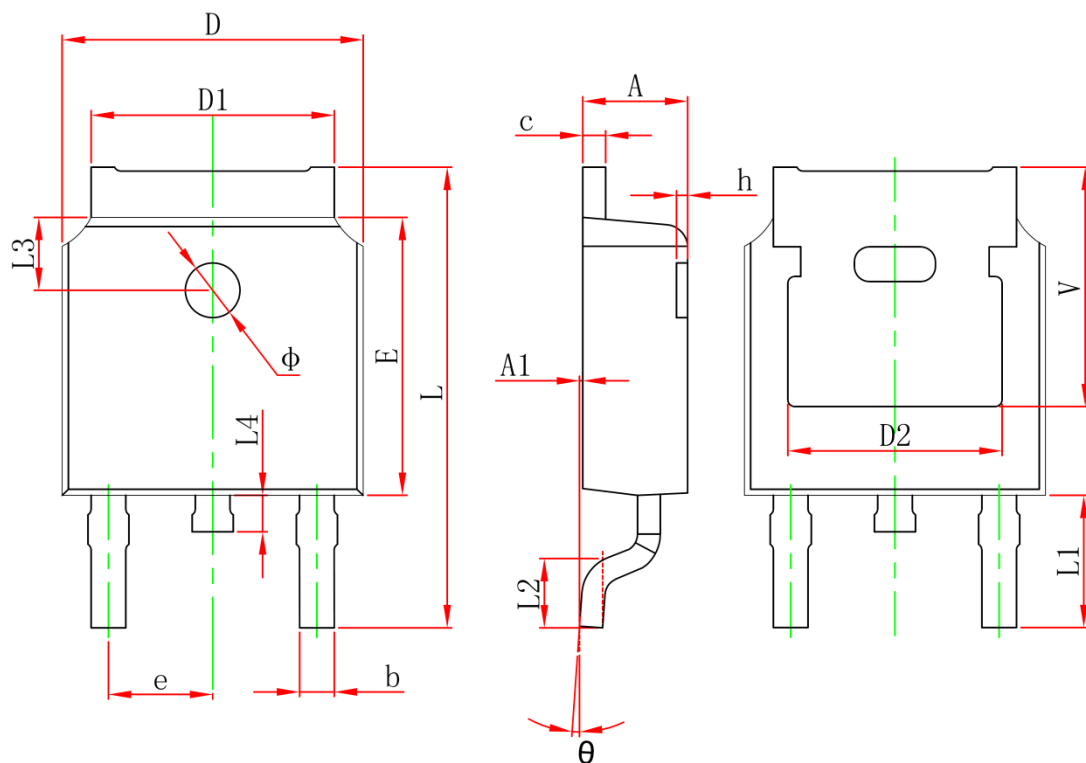
Rdson- Drain Current



Source- Drain Diode Forward



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
ϕ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	